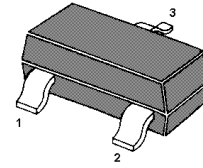


MMBT5B1197

PNP Silicon Epitaxial Planar Transistor

Low frequency transistor

The transistor is subdivided into two groups Q and R according to its DC current gain.



1.BASE 2.EMITTER 3.COLLECTOR
SOT-23 Plastic Package

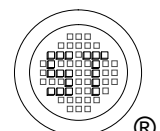
Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Collector Base Voltage	$-V_{\text{CBO}}$	40	V
Collector Emitter Voltage	$-V_{\text{CEO}}$	32	V
Emitter Base Voltage	$-V_{\text{EBO}}$	5	V
Collector Current	$-I_{\text{C}}$	800	mA
Power Dissipation	P_{tot}	200	mW
Junction Temperature	T_{j}	150	$^\circ\text{C}$
Storage Temperature Range	T_{Stg}	-55 to +150	$^\circ\text{C}$

Thermal Characteristics

Parameter	Symbol	Max.	Unit
Thermal Resistance from Junction to Ambient ¹⁾	$R_{\theta\text{JA}}$	625	$^\circ\text{C/W}$

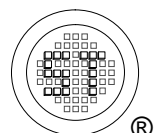
¹⁾ Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.



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Characteristics at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Min.	Max.	Unit
DC Current Gain at $-V_{CE} = 3\text{ V}$, $-I_C = 100\text{ mA}$	Q	120	270	-
	R	180	390	-
Collector Cutoff Current at $-V_{CB} = 20\text{ V}$	$-I_{CBO}$	-	0.5	μA
Emitter Cutoff Current at $-V_{EB} = 4\text{ V}$	$-I_{EBO}$	-	0.5	μA
Collector Base Breakdown Voltage at $-I_C = 50\text{ }\mu\text{A}$	$-V_{(BR)CBO}$	40	-	V
Collector Emitter Breakdown Voltage at $-I_C = 1\text{ mA}$	$-V_{(BR)CEO}$	32	-	V
Emitter Base Breakdown Voltage at $-I_E = 50\text{ }\mu\text{A}$	$-V_{(BR)EBO}$	5	-	V
Collector Saturation Voltage at $-I_C = 500\text{ mA}$, $-I_B = 50\text{ mA}$	$-V_{CE(sat)}$	-	0.5	V
Output Capacitance at $-V_{CB} = 10\text{ V}$, $I_E = 0\text{ A}$, $f = 1\text{ MHz}$	C_{ob}	-	30	pF
Transition Frequency at $-V_{CE} = 5\text{ V}$, $I_E = 50\text{ mA}$, $f = 100\text{ MHz}$	f_T	50	-	MHz



Electrical Characteristics Curves

Fig. 1 Output Characteristics Curve

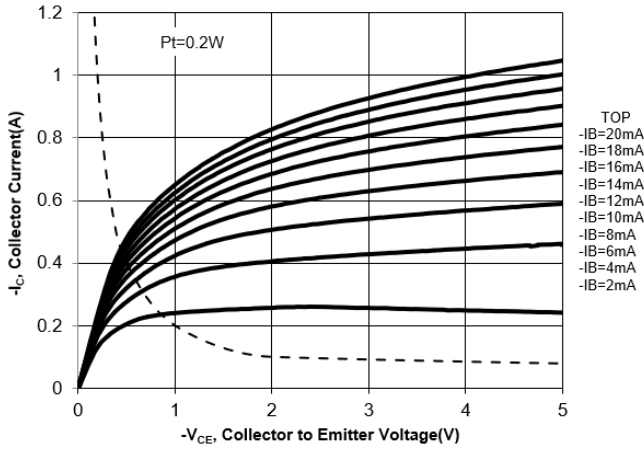


Fig. 2 Collector Current vs. Base to Emitter Voltage

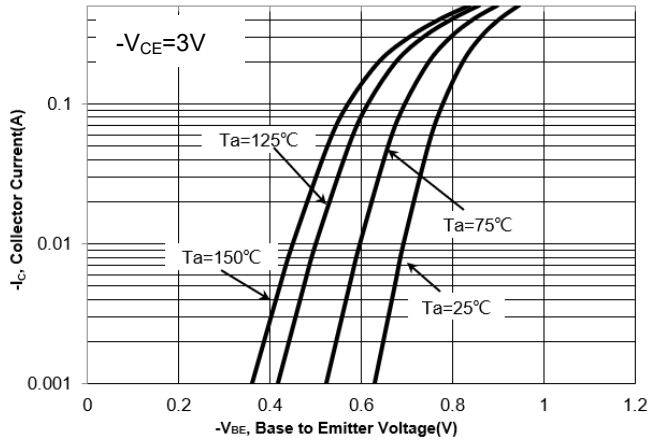


Fig. 3 V_{BESAT} vs. Collector Current

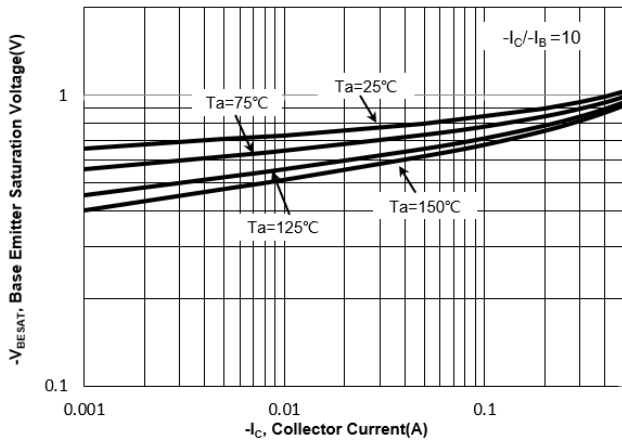


Fig. 4 $h_{FE,DC}$ Current Gain vs. Collector Current

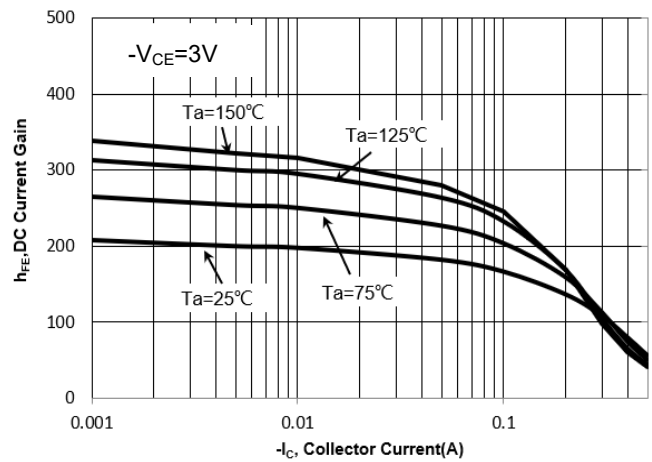


Fig. 5 V_{CESAT} vs. Collector Current

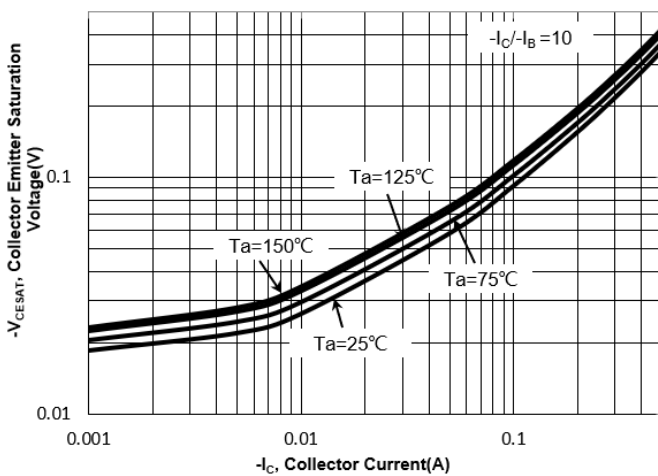
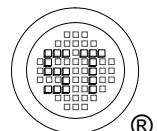
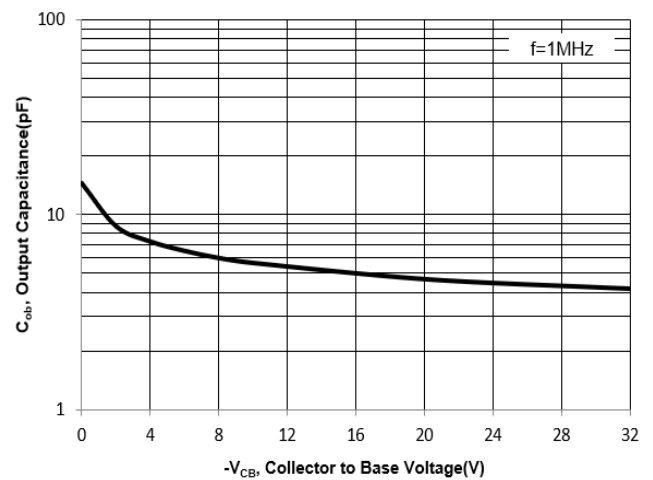


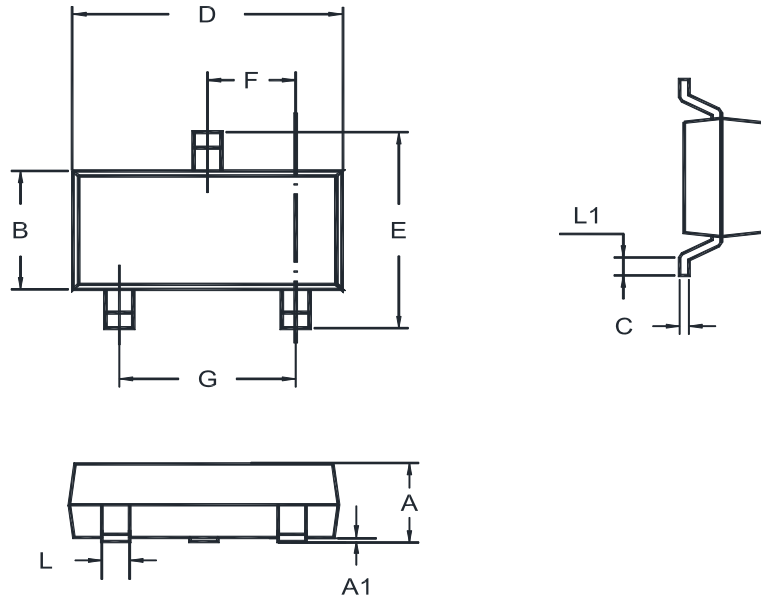
Fig. 6 Output Capacitance



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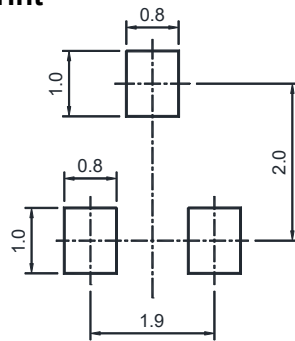
Package Outline (Dimensions in mm)

SOT-23



Unit	A	A1	B	C	D	E	F	G	L	L1
mm	1.20	0.100	1.40	0.19	3.04	2.6	1.02	2.04	0.51	0.2
	0.89	0.013	1.20	0.08	2.80	2.2	0.89	1.78	0.37	MIN

Recommended Soldering Footprint



Packing information

Package	Tape Width (mm)	Pitch		Reel Size		Per Reel Packing Quantity
		mm	inch	mm	inch	
SOT-23	8	4 ± 0.1	0.157 ± 0.004	178	7	3,000

Marking information

" *** " = Part No.
 MMBTSB1197Q/R=B9C/B9D
 " YM " = Date Code Marking
 " Y " = Year
 " M " = Month
 Font type: Arial

